

L8: (1) 4 same 7
 L9: (18) ("5872401" | "6068884" | "6077764" | "6147009" | "6158845" | "621
 L10: (2) 6348421.pn.
 L12: (1774) 2 3 4
 L14: (6) 11 and 13
 L13: (6) 12 near 2 5
 L11: (28) 8 9 10
 L15: (875) sioc
 L16: (2394) 2 3 4 15
 L17: (10) 16 near 2 5
 L18: (2) 17 not 13
 L19: (701929) oxygen
 L21: (1) 11 not 20
 L20: (27) 11 and 19
 L22: (20) 20 and 5
 L23: (6) 11 not 22
 L24: (45) 16 near 8 5
 L25: (17) 24 with 6
 L26: (10) 25 not 11
 L27: (18) ("5872401" | "6068884" | "6077764" | "6147009" | "6158845" | "621
 L28: (201) 4.clm
 L29: (860) 7.clm
 L30: (3) 28 same 29
 L31: (10) 29 and 29
 L32: (4) ("5141897" | "5980637" | "5994778" | "6333255").PN.
 L33: (9) 6441491.DRPN.

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Default operator: OR				
28 and 29				

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9	<input type="checkbox"/> Calabay, Wil.	US 6492731 20021 9	Composite low dielectric constant film for in	257/758 257/411	<input type="checkbox"/>	US 6492731	<input type="checkbox"/>						
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